Examination questions for the lectures "Magnetic materials in nanoelectronics - properties and fabrication"

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- At the beginning you will be given four questions from the list shown below<sup>1</sup>
- The oral examination will be conducted in English but the language proficiency *will not* influence the grading
- After receiving the set of questions you will be given 5 minutes to prepare the answers
- You will be allowed to use paper and pen to prepare your answers and during the examination
- During the preparation of the answers you will be allowed to have two DIN A4 sheets (4 *numbered* pages) with *hand-written* notes (no copies; one set of notes per one examinee) which you should present to me for marking
- As the exam will not generate any written record you are encouraged to designate a person (not the examinee) who will observe the course of the examination as your representative

The questions:

- 1. Unpaired charges in conductors; surface charges as the source of internal electric field (1-D case). (lecture no. 1)
- 2. Potential of an electrode on a uniform, isotropic conductor occupying a half-space. (lecture no. 1)
- 3. Potential of two electrodes and a four point probe for thin conducting films. (lecture no. 1)
- 4. Accuracy, precision; Johnson noise. (lecture no. 1)
- 5. Magnetic dipole moment and magnetization. (lecture no. 2)
- 6. Magnetic flux density and magnetic field strength. (lecture no. 2)

<sup>&</sup>lt;sup>1</sup>during the exam you will have to answer four questions from the list; no other questions from the list will appear in the exam although I may ask you some additional questions concerning the topic refereed to by the initial questions

- 7. Susceptibility, classification of magnetic and ferromagnetic materials. (lecture no. 2)
- Vibrating sample magnetometer and lock-in principle. (lecture no. 2)
- 9. Magnetocrystalline anisotropy. (lecture no. 3)
- 10. Shape anisotropy. (lecture no. 3)
- 11. Surface and exchange anisotropy. (lecture no. 3)
- 12. Stress anisotropy. (lecture no. 3)
- 13. Dynamic effects in magnetic hysteresis losses; static limit. (lecture no. 4)
- 14. Complex susceptibility and dissipation. (lecture no. 4)
- 15. Preisach model of hysteresis. (lecture no. 4)
- 16. Size effects in resistivity. (lecture no. 5)
- 17. Magnons and resistivity. (lecture no. 5)
- 18. Mott two current model. (lecture no. 5)
- 19. GMR resistors network model. (lecture no. 5)
- 20. GMR Boltzmann transport equation and results of Barnaś model; angular dependence. (lecture no. 5)
- 21. RKKY coupling; GMR systems with coupling (RKKY, exchange). (lecture no. 5)
- 22. Typical GMR systems (different coercivities of the layers, systems with coupling, alternating anisotropies,  $G^2MR$ ). (lecture no. 5)
- 23. Various GMR sensors (field, angle, with memory); sensitivity versus RKKY-coupling energy. (lecture no. 6)
- 24. Magnetoresistive random-access memory (writing process, readout). (lecture no. 6)
- 25. Spin torque transfer switching. (lecture no. 6)
- 26. Boltzmann velocity distribution. (lecture no. 7)
- 27. Mean free path of gas molecules and quality of vacuum. (lecture no. 7)

- 28. Impingement rate, sticking coefficient, and monolayer formation time. (lecture no. 7)
- 29. Vapor pressure, evaporation rate (Hertz-Knudsen equation). (lecture no. 7)
- 30. Knudsen cell and thickness profile from a small surface source. (lecture no. 7)
- 31. Sputtering process (physical): yield, energy distribution of sputtered atoms, angular distribution etc. (lecture no. 7)
- 32. Evaporation versus sputtering. (lecture no. 7)
- 33. Potential of adatom on a crystal surface and surface diffusion. (lecture no. 8)
- 34. Epitaxy. (lecture no. 8)
- 35. Basic modes of thin film growth. (lecture no. 8)
- 36. Zone model of thin film growth. (lecture no. 8)